

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire, and
an insulating film over the conducting wire,
wherein the integrated circuit and the antenna are formed over the substrate to
be electrically connected to each other, and
fine particles of a soft magnetic material are included in the insulating film.
2. (Original) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire, and
a resin film over the conducting wire,
wherein the integrated circuit and the antenna are formed over the substrate to
be electrically connected to each other, and
fine particles of a soft magnetic material are included in the resin film.
3. (Original) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire,
a first insulating film covering the conducting wire and the thin film transistor, and

a second insulating film over the first insulating film covering the conducting wire, wherein the integrated circuit and the antenna are formed over the substrate to be electrically connected to each other, and fine particles of a soft magnetic material are included in the second insulating film.

4. (Original) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire,
an insulating film covering the conducting wire and the thin film transistor, and
a resin film over the insulating film covering the conducting wire,
wherein the integrated circuit and the antenna are formed over the substrate to be electrically connected to each other, and
fine particles of a soft magnetic material are included in the resin film.

5. (Withdrawn) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire,
a first insulating film covering the thin film transistor,
a second insulating film over the first insulating film,
the conducting wire over the second insulating film, and
a third insulating film over the conducting wire,
wherein the integrated circuit and the antenna are formed over the substrate to be electrically connected to each other, and
fine particles of a soft magnetic material are included in the second insulating film and the third insulating film.

6. (Withdrawn) A semiconductor device comprising:

a substrate,

an integrated circuit including a thin film transistor,

an antenna having a conducting wire,

a first insulating film covering the thin film transistor,

a second insulating film over the first insulating film,

the conducting wire over the second insulating film,

a third insulating film over the conducting wire, and

a fourth insulating film over the third insulating film,

wherein the integrated circuit and the antenna are formed over the substrate to be electrically connected to each other, and

fine particles of a soft magnetic material are included in the second insulating film and the fourth insulating film.

7. (Withdrawn) A semiconductor device comprising:

a substrate,

an integrated circuit including a thin film transistor,

an antenna having a conducting wire,

a first insulating film at least covering the conducting wire, and

a second insulating film covering the first insulating film and the thin film transistor,

wherein the integrated circuit and the antenna are formed over the substrate to be electrically connected to each other,

the conducting wire is formed from a same material as a gate electrode of the thin film transistor, and is formed on a same layer, and

fine particles of a soft magnetic material are included in the first insulating film.

8. (Currently Amended) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire, ~~[[and]]~~
a first insulating film covering the conducting wire and the thin film transistor, and
~~[[an]]~~ a second insulating film at least ~~contacts with~~ adjacent to a side of the
conducting wire by interposing the first insulating film therebetween,
wherein the integrated circuit and the antenna are formed over the substrate to
be electrically connected to each other, and
fine particles of a soft magnetic material are included in the second insulating
film.

9. (Currently Amended) A semiconductor device comprising:
a substrate,
an integrated circuit including a thin film transistor,
an antenna having a conducting wire, ~~[[and]]~~
an insulating film covering the conducting wire and the thin film transistor, and
a resin film at least ~~contacts with~~ adjacent to a side of the conducting wire by
interposing the insulating film therebetween,
wherein the integrated circuit and the antenna are formed over the substrate to
be electrically connected to each other, and
fine particles of a soft magnetic material are included in the resin film.

10. (Original) The semiconductor device according to any one of Claims 1 to 9,
wherein the integrated circuit and the antenna are formed over a flexible substrate.

11. (Original) The semiconductor device according to any one of Claims 1 to 9, wherein the conducting wire is formed by an electroplating method, an electroless plating method, a printing method, or a droplet discharging method.

12. (Original) The semiconductor device according to any one of Claims 1 to 9, wherein the conducting wire includes a first conductor and a second conductor covering the first conductor.

13. (Original) The semiconductor device according to Claim 12, wherein the second conductor is formed by an electroplating method, an electroless plating method, or a droplet discharging method.

14. (Original) The semiconductor device according to Claims 1 to 9, wherein the soft magnetic material is Fe; Co; Ni; an alloy including at least one of Fe, Co, and Ni; $3Y_2O_3 \cdot 5Fe_2O_3$ (YIG); Fe_2O_3 ; Fe-Si-Al alloy; Fe-Cr alloy; FeP alloy; a permalloy in which Ni or Ni-Fe alloy is added with at least one of Mo, Cu, Cr, and Nb; or a soft ferrite.